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□ Active □ St.1: (5) memory with ((back adj gate) near5 □ St.2: (1) memory with substrate with (potential or bias or volt53) with chang\$3 with (back adj gate) and [Ps. PGPUB; USPAT; USOCR; EPO, PPO, DERWENT; IBM_TDB □ BRS	1 1				Search List Browne Queue Que		
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